

L Number	Hits	Search Text	DB	Time stamp
1	1	("6461932").PN.	USPAT; US_PGPUB	2004/06/08 09:41
39	18512	semiconductor and planarization	USPAT; US_PGPUB	2004/06/08 10:02
41	713	(semiconductor and planarization) and substantially adj flat	USPAT; US_PGPUB	2004/06/08 10:02
42	166	((semiconductor and planarization) and substantially adj flat) and recess	USPAT; US_PGPUB	2004/06/08 10:02
35	1	("5663090").PN.	USPAT; US_PGPUB	2004/06/08 10:02
36	1	("6358793").PN.	USPAT; US_PGPUB	2004/06/08 10:02
37	6	((5,405,813") or (6,146,968") or (6,228,711") or (6,235,605") or (6,303,430") or (6,417,066")).PN.	USPAT	2004/06/08 10:02
38	2	((("5,405,813") or ("6,146,968") or ("6,228,711") or ("6,235,605") or ("6,303,430") or ("6,417,066"))).PN.) and (planar flat)	USPAT; US_PGPUB	2004/06/08 10:02
43	24	((semiconductor and planarization) and substantially adj flat) and substrate near4 recess	USPAT; US_PGPUB	2004/06/08 10:02
45	8	((("6278153") or ("6,117,486") or ("6,228,711") or ("6,461,932") or ("2,538,878") or ("5,677,001") or ("6,046,083") or ("6,326,282")).PN.	USPAT; US_PGPUB	2004/06/08 10:02
46	5	okada and mask and asperity	USPAT; US_PGPUB	2004/06/08 10:02
51	651	((427/240,385.5) or (257/510,520,621,622,752,774) or (438/591,623,626,631,677,685)).CCLS. and @pd>20031203	USPAT; US_PGPUB	2004/06/08 10:03
52	919	dual near3 (damocene damascene) and @pd>20031203	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 10:04
53	15947	spin?coat\$3 spin adj coat\$3 and @pd>20031203	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 10:04
55	106	stress near3 buffer and @pd>20031203	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/08 10:05